

SAM™ data sheet SAM-800-10-1ps-x, λ = 800 nm

High reflection band λ = 785 820 nmAbsorbance A_0 = 10 %Modulation depth ΔR = 6%Non-saturable loss A_{ns} = 4 %Saturation fluence Φ_{sat} = 70 µJ/cm²Relaxation time constant $\tau \sim 1$ psDamage threshold Φ = 1.5 mJ/cm²Chip area4.0 mm x 4.0 mm; other dimensions on requestKein the constant450 µm
Modulation depth $\Delta R = 6\%$ Non-saturable loss $A_{ns} = 4\%$ Saturation fluence $\Phi_{sat} = 70 \mu J/cm^2$ Relaxation time constant $\tau \sim 1 ps$ Damage threshold $\Phi = 1.5 m J/cm^2$ Chip area $4.0 mm x 4.0 mm;$ other dimensions on request
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Chip thickness 450 µm
Protection the SAM is protected with a dielectric front layer
Mounting option x denotes the type of mounting as follows: x = 0 unmounted x = 12.7 g glued on a gold plated Cu-cylinder with 12.7 mm Ø

x = 12.7 gglued on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 25.4 gglued on a gold plated Cu-cylinder with 25.4 mm \varnothing x = 12.7 ssoldered on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 25.4 ssoldered on a gold plated Cu-cylinder with 25.4 mm \varnothing x = 25.0 wsoldered on a water cooled Cu-cylinder with 25.0 mm \varnothing x = FCmounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance





